

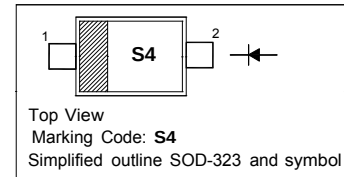
Surface Mount Schottky Barrier Diodes

Features

- Low Forward Voltage

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	40 30 20	V
Reverse Voltage	V_R	40 30 20	V
Average Forward Rectified Current	$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at $t = 1\text{ s}$	I_{FSM}	2	A
Power Dissipation	P_{tot}	200	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	40 30 20	- - -	- - -	V
Reverse Leakage Current at $V_R = 30\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 10\text{ V}$	I_R	- - -	- - -	5 5 5	μA
Forward Voltage at $I_F = 20\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	- -	- -	0.37 0.6	V
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	-	50	-	pF
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$, $t_{rr} = 0.1\text{ I}_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	10	-	ns

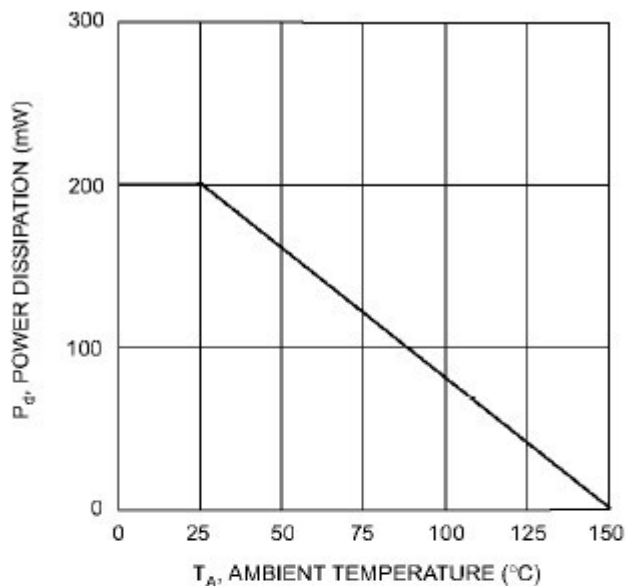


Fig. 1 Power Derating Curve

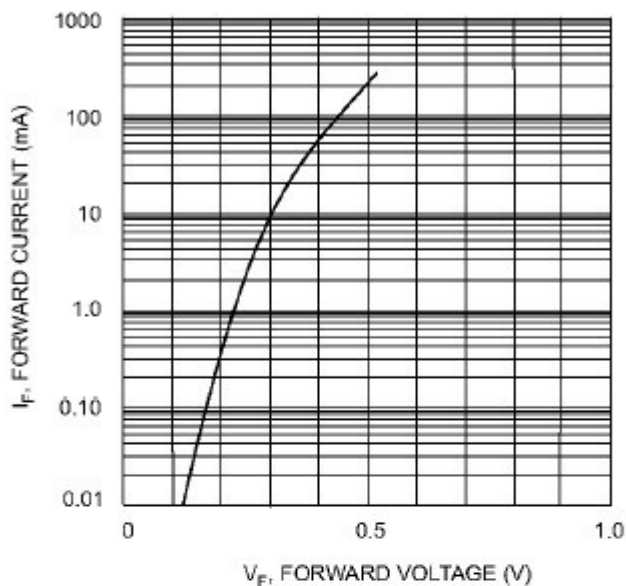


Fig. 2 Typical Forward Characteristics

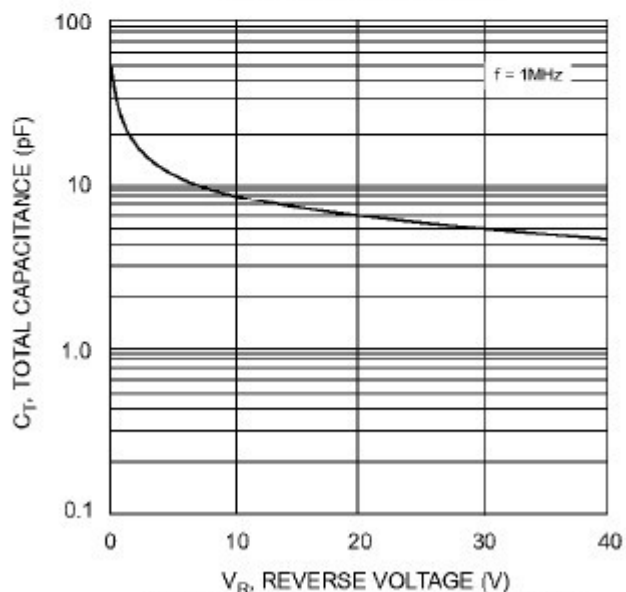


Fig. 3 Total Capacitance vs Reverse Voltage